



12V NPN HIGH GAIN TRANSISTOR IN SOT89

Features

- BV_{CEO} > 12V
- Low Saturation Voltage V_{CE(sat)} < 38mV @ 1A
- I_C = 6.5A High Continuous Current
- P_D = 2.4W Power Dissipation
- $R_{sat} = 25m\Omega$ for a Low Equivalent On-Resistance
- Complementary part number: ZXTP25012EZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.05 grams (Approximate)

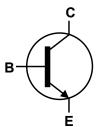
Application

- LED driving
- Motor driving
- Boost converters
- Royer converters
- Camera strobe
- · MOSFET gate drivers

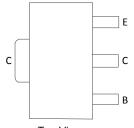
Application



Top View



Device Symbol



Top View Pin Out

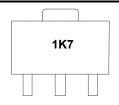
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTN25012EZTA	Standard	1K7	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



1K7 = Product Type Marking Code

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Document number: DS33689 Rev. 3 - 2

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Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	12	V
Emitter-Collector Voltage (reverse blocking)	V _{ECX}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6.5	Α
Peak Pulse Collector Current (single pulse)	I _{CM}	15	Α
Base Current	I _B	1	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P _D	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.8 14.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P _D	2.4 19.2	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	P _D	4.46 35.7	W mW/°C
Power Dissipation (Note 9) Linear Derating Factor	P _D	19.2 153	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJA}	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	R _{θJC}	7.95	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

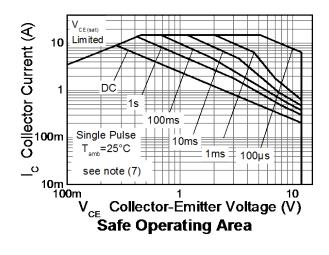
Notes:

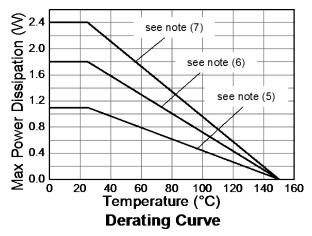
- 5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.

 6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.
- 8. Same as note (5), except the device is measured at t<5 seconds.
 9. Junction to case (collector tab). Typical.



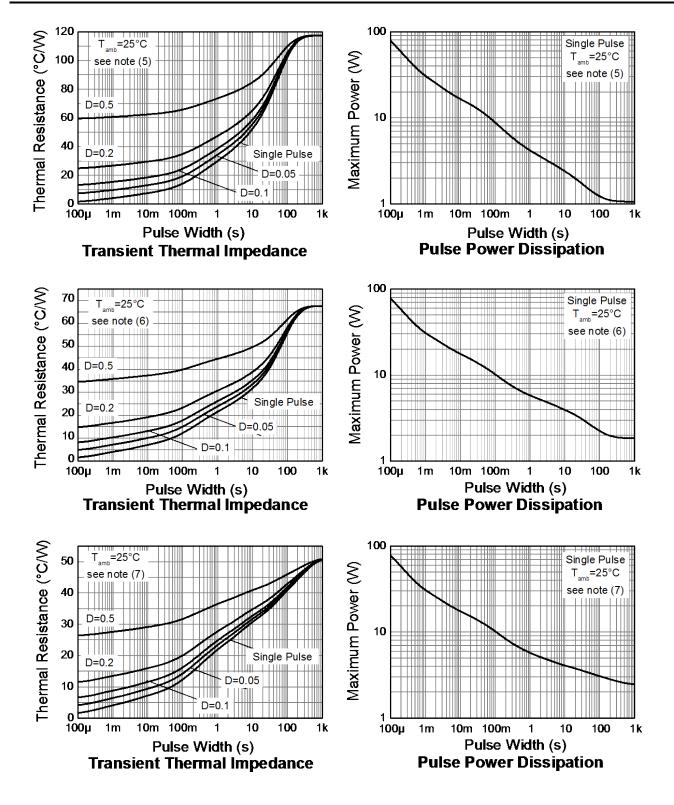
Thermal Characteristics and Derating Information







Thermal Characteristics and Derating Information (cont.)





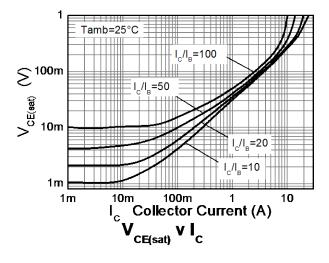
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

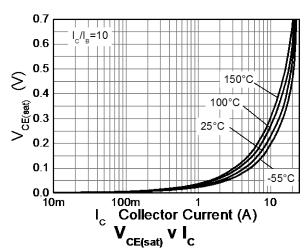
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	20	40	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	12	17	_	V	I _C = 10mA
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECX}	6	8	_	V	I_E = 100mA, R_{BC} < 1k Ω or 0.25V > V_{BC} > -0.25V
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECO}	4.5	5.5	_	V	I _E = 100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.3	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_	1 —	50 0.5	nA μA	V _{CB} = 20V V _{CB} = 20V, T _A = +100°C
Collector-Emitter Cutoff Current	I _{CEX}	_	-	100	nA	V_{CE} = 20V, R_{BE} < 1kΩ or -1V < V_{BE} < 0.25V
Emitter Cutoff Current	I _{EBO}	_	1	50	nA	V _{EB} = 5.6V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	31 50 70 90 200	38 60 85 130 270	mV	I_C = 1A, I_B = 100mA I_C = 1A, I_B = 10mA I_C = 2A, I_B = 40mA I_C = 2A, I_B = 20mA I_C = 6.5A, I_B = 130mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	950	1050	mV	I _C = 6.5A, I _B = 130mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	840	950	mV	I _C = 6.5A, V _{CE} = 2V
DC Current Gain (Note 10)	h _{FE}	500 500 185 30	800 750 250 50	1500 — — —	_	I _C = 10mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 6.5A, V _{CE} = 2V I _C = 15A, V _{CE} = 2V
Transitional frequency	f⊤	_	260	_	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz
Input Capacitance	Ci _{bo}	_	137	250	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	25	35	pF	V _{CB} = 10V, f = 1MHz
Delay time	t _d	_	71	_	ns	
Rise time	t _r	_	70	_	ns	V _{CC} = 10V, I _C = 1A,
Storage time	ts	_	233	_	ns	I _{B1} = -I _{B2} = 10mA
Fall time	t _f	_	72	_	ns	

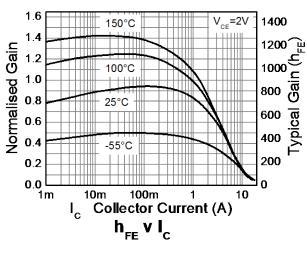
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

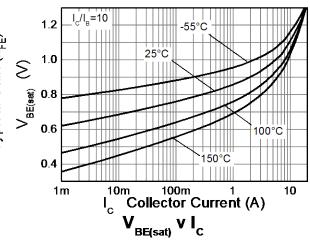


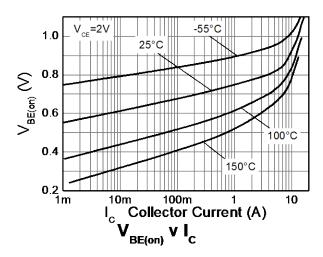
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)









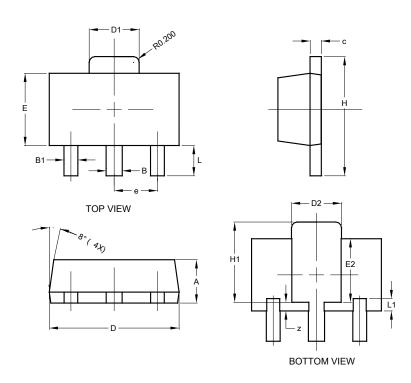




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

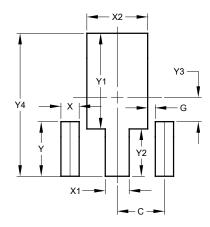


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	ı	1.50		
Η	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value	
פווטופוופוווט	(in mm)	
С	1.500	
G	0.244	
Х	0.580	
X1	0.760	
X2	1.933	
Υ	1.730	
Y1	3.030	
Y2	1.500	
Y3	0.770	
Y4	4.530	



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